



# Nb<sub>3</sub>Sn films grown by low temperature co-sputtering for SRF cavity application

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**TOSCA** collaboration meeting

# Possible superconducting materials for RF cavities



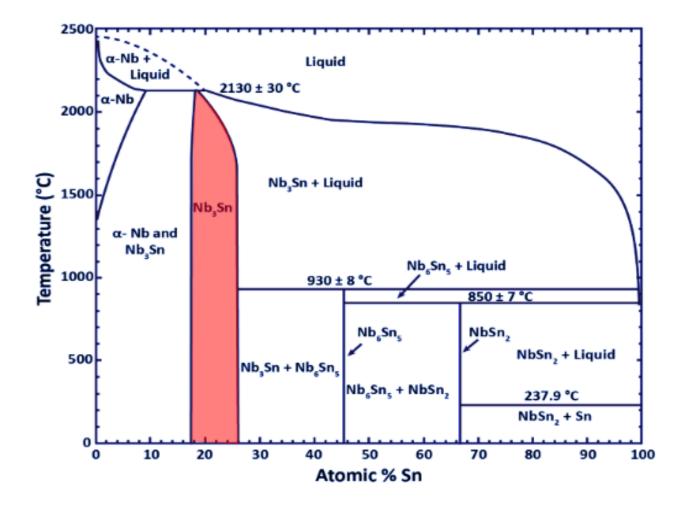


Material	Critical Temp. T <sub>c</sub> [K]	Normal- state resistivity ρ <sub>n</sub> [μΩcm]	Critical Field H <sub>c</sub> (0) [T]	Lower Critical field H <sub>c1</sub> (0) [T]	Upper Critical field H <sub>c2</sub> (0) [T]	Penetration depth λ(0) [nm]	Δ [meV]	Туре
Nb	9.23	2	0.2	0.18	0.28	40	1.5	II
Pb	7.2		0.08	N/A	N/A	48		I
NbN	16.2	70	0.23	0.02	15	200-350	2.6	II, B1 comp.
NbTiN	17.3	35		0.03		150-200		II, B1 comp.
Nb <sub>3</sub> Sn	18	20	0.54	0.05	30	80-100	3.1	II, A15
V <sub>3</sub> Si	17				24.5	179		II, A15
Mo <sub>3</sub> Re	15		0.43	0.03	3.5	140		II, A15
MgB <sub>2</sub>	40	0.1-10	0.43	0.03	3.5-60	140	2.3/7.2	II- 2 gaps
YBCO	93		1.4	0.01	100	150	20	d-wave
Pnictides	30-55		0.5-0.9	30	>100	200	10-20	

## Nb-Sn phase diagram





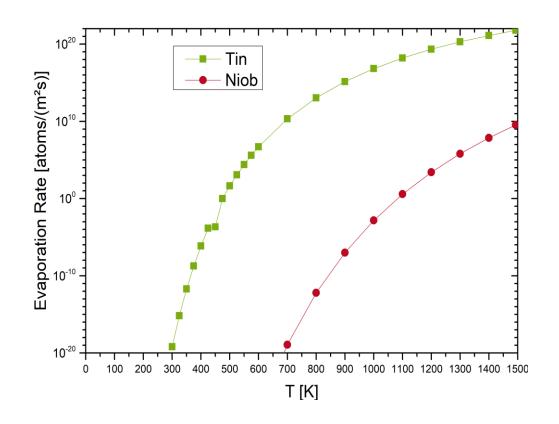


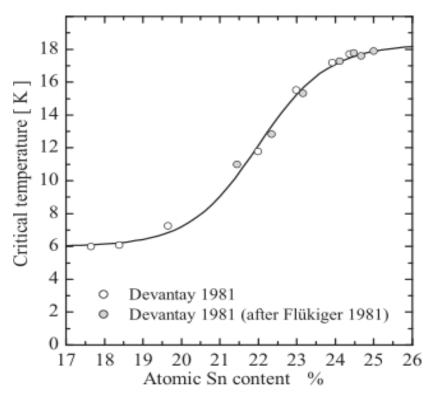
Charlesworth JP, Macphail I, Madsen PE., Journal of Materials Science. 1970 Jul 1;5(7):580-603.

# **Challenge: Vapor-pressure of Sn**









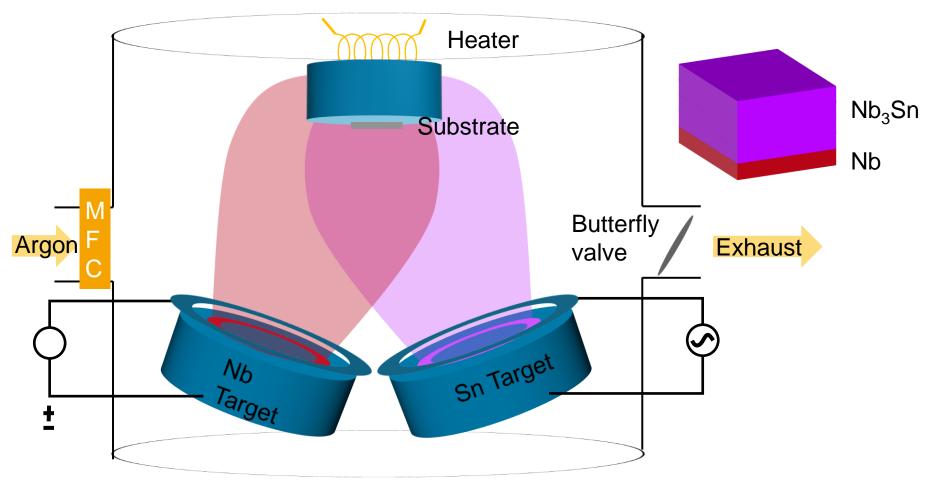
Literature results for the critical temperature as functions of Nb–Sn composition.

A Godeke 2006 Supercond. Sci. Technol. 19 R68

# TU Darmstadt approach: Nb<sub>3</sub>Sn co-sputtering







# Nb<sub>3</sub>Sn cavity roadmap





- Optimization of the sputtering parameters (sputter power, substrate temperature, etc.) on fused silica substrate
- 2. Adaptation of the growth parameters (further optimization of growth temperature etc.) for copper substrate
- 3. Upscaling of the sputtering process to the cavity geometry:
  - a. Optimizing the sputtering parameters for the new (larger) sputtering chamber
  - b. Design and production of the mini double ring magnetron for cavity sputtering
  - c. Inner coating of Cu cavities

# Nb<sub>3</sub>Sn cavity roadmap





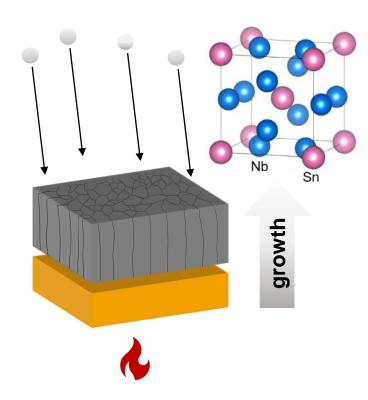
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# Physical properties of Nb<sub>3</sub>Sn films grown on Cu

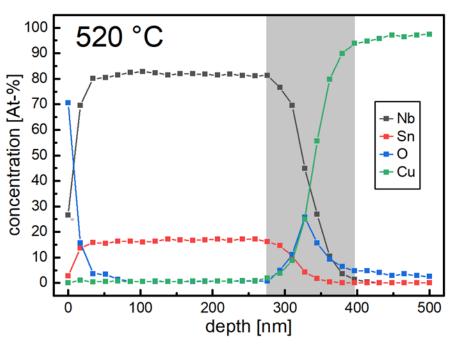




#### **XPS Depth Profile**



< 520 °C @ 60 min.

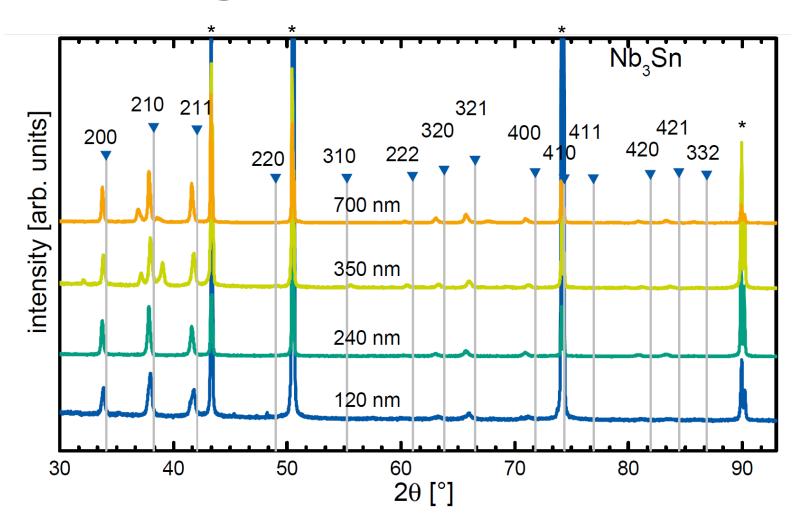


Nb, Sn, Cu and O content measured by XPS plotted as a function of the distance from the surface (0 nm) for a sample deposited at 520 °C. They left part (0-275 nm) is the Nb $_3$ Sn film. The interface region (~120 nm broad) between the film and the Cu substrate is marked by the grey area. The right side (starting at ~ 400 nm) represents the copper substrate.

# Physical properties of Nb<sub>3</sub>Sn films grown on Cu





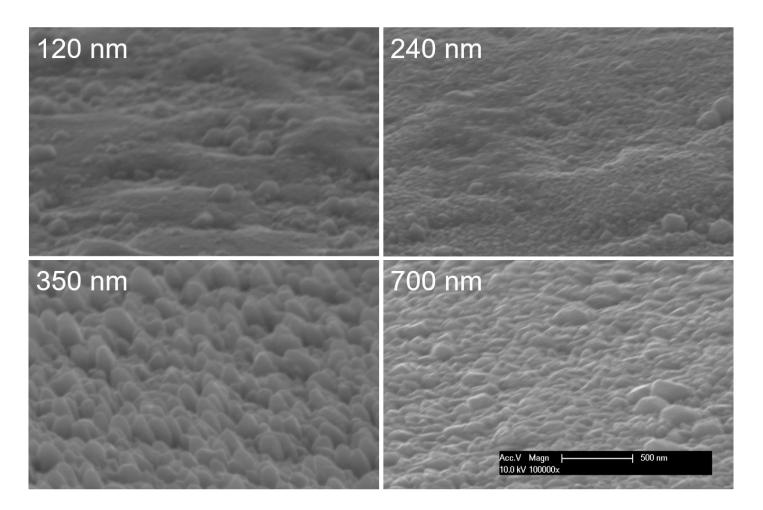


XRD patterns of Nb<sub>3</sub>Sn thin films grown on copper substrates at elevated temperature (480 °C). The coating duration is increased from 10 min to 60 min resulting in 120 nm to 700 nm film thickness. Calculated Nb<sub>3</sub>Sn Bragg peaks are marked by tip down triangles in their respective intensity. The Cu substrate peaks are marked with \*. Additional reflections appear for the samples of 350 nm and 700 nm thickness.

## Grain size, surface roughness





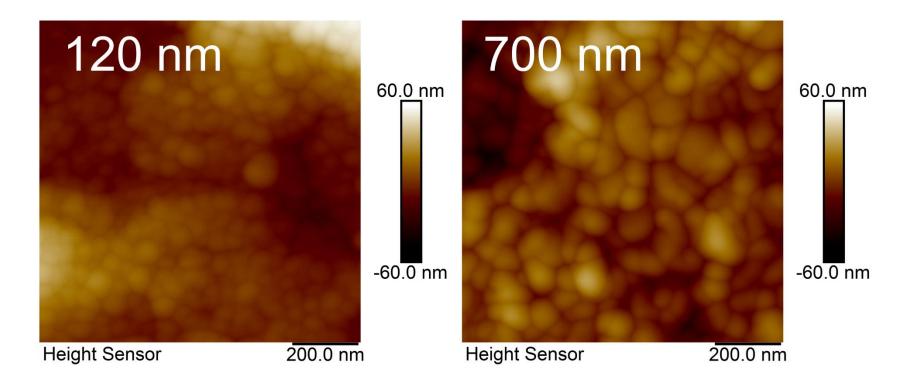


SEM images of  $Nb_3Sn$  thin films synthesized by cosputtering on copper substrates. The coating duration was increased from 10 min to 60 min (10 min, 20 min, 30 min and 60 min) resulting in the indicated 120 nm to 700 nm film thicknesses.

### Grain size, surface roughness





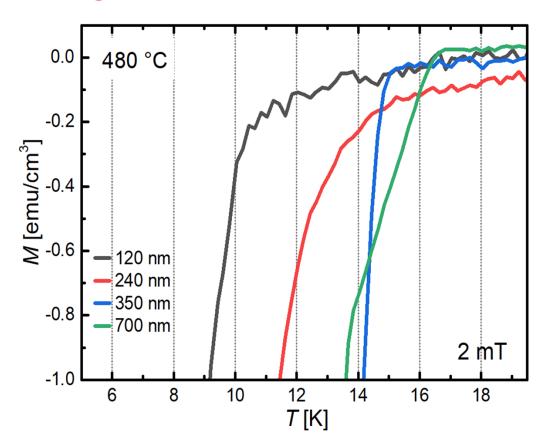


AFM topography images of Nb<sub>3</sub>Sn thin films synthesized by co-sputtering on copper substrates. The coating duration was 10 min and 60 min resulting in 120 nm and 700 nm film thickness, respectively.

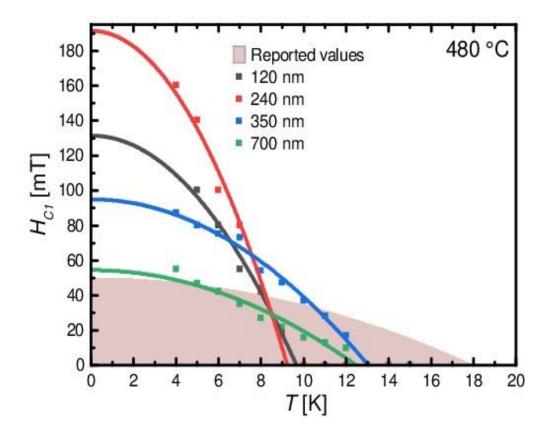




#### **Magnetization Parallel to Field**



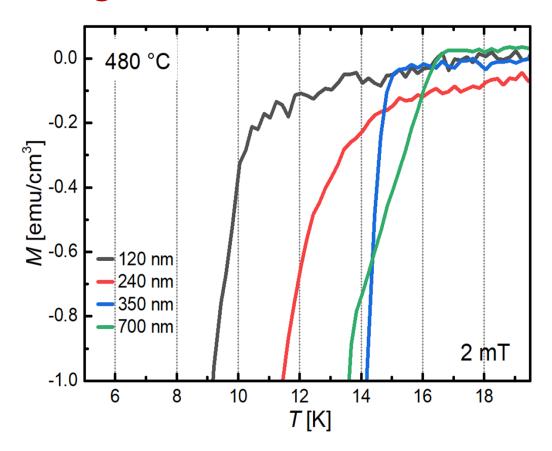
#### Temperature dependence of H<sub>c1</sub>







#### **Magnetization Parallel to Field**



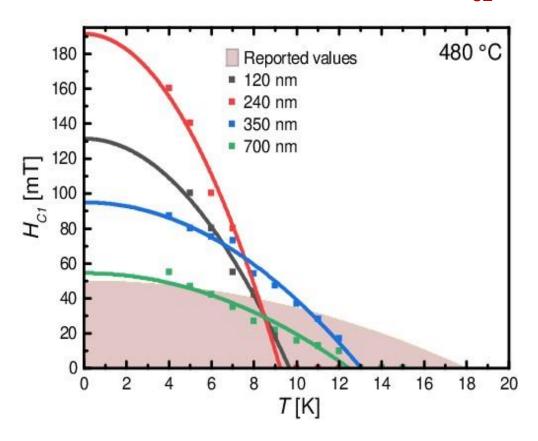
- Increasing thickness beneficial for critical temperature
- T<sub>c.0</sub>=16.8 K @ 480 °C!
- 120 nm < λ (140 nm), still shielding</li>





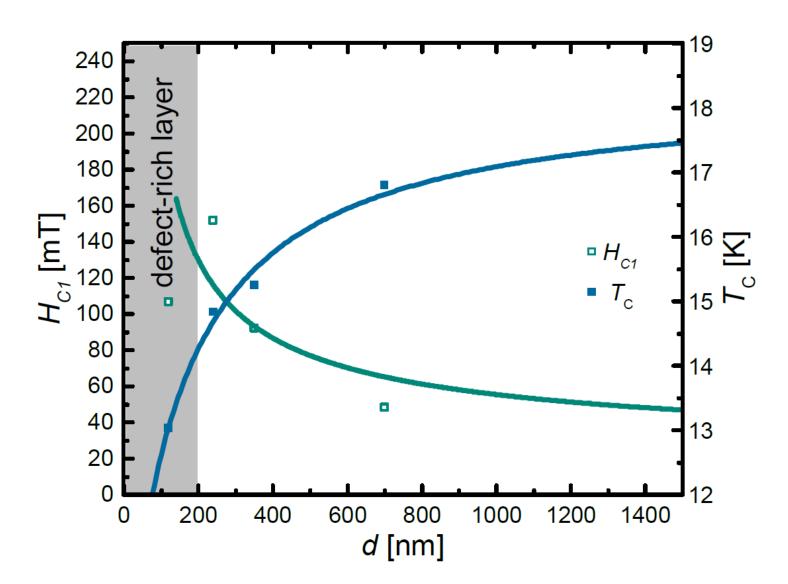
#### Temperature dependence of H<sub>c1</sub>

- Bulk performance for 700 nm thickness.
- Below 700 nm enhancement of  $H_{c1}$  (known below  $\lambda$ =140 nm)
- Decreasing film thickness beneficial for H<sub>c1</sub>









Critical temperature  $T_c$  determined from M-T measurements and critical field  $H_{c1}$  from M-H measurements at 4K of Nb<sub>3</sub>Sn thin films on copper substrates as a function of film thickness.

The grey box marks the defect-rich layer in the beginning of the growth process leading to low performance. The solid lines provide a guide to the eye.

# Physical properties of Nb<sub>3</sub>Sn films grown on Cu – Conclusions





The thin film synthesis results in Nb<sub>3</sub>Sn layers with overall highly beneficial properties for their application as coatings in copper based SRF cavities.

At processing temperatures where copper diffusion is negligible, around 480 °C, a critical temperature of 16.8K can be achieved. At the same time,  $H_{c1}$  is enhanced which enhances the applicable acceleration gradients. Low surface roughness and high mechanical stability further makes these coatings excellent candidates for cavity applications.

# Nb<sub>3</sub>Sn cavity roadmap



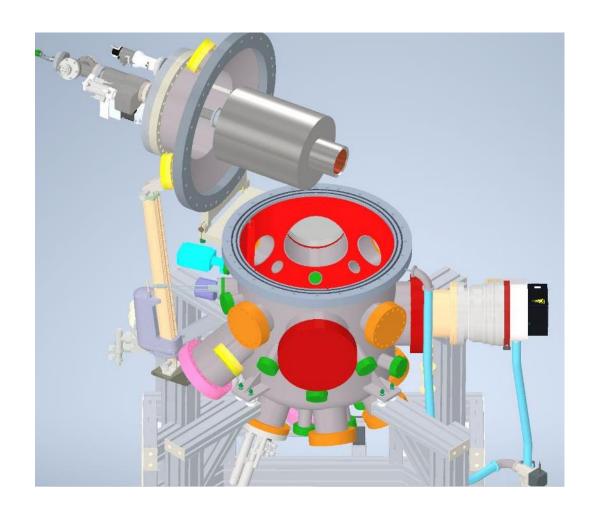


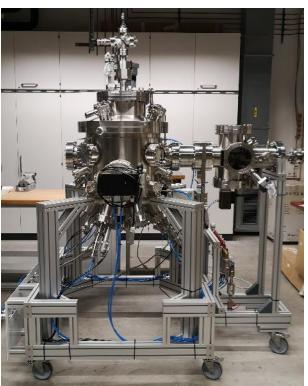
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## Upscaling to copper cavities







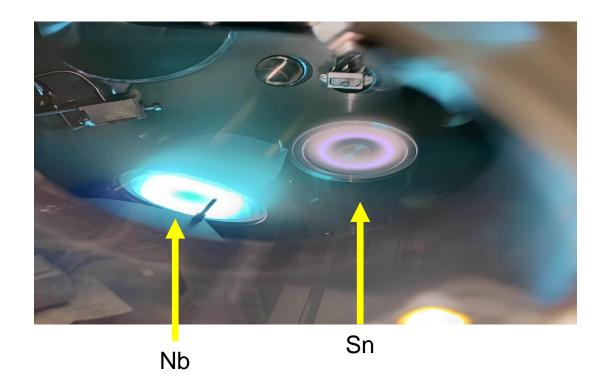


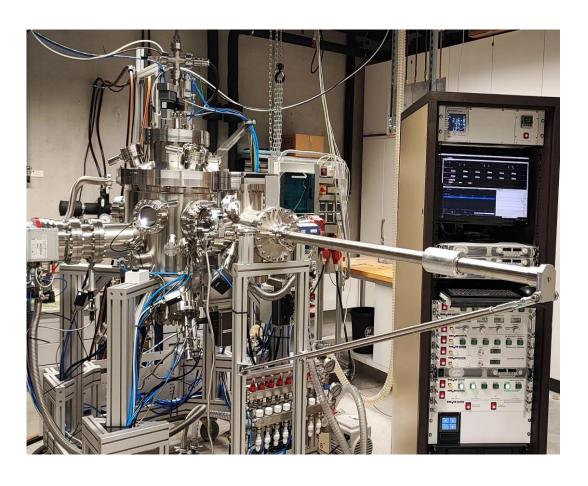


## Upscaling to copper cavities







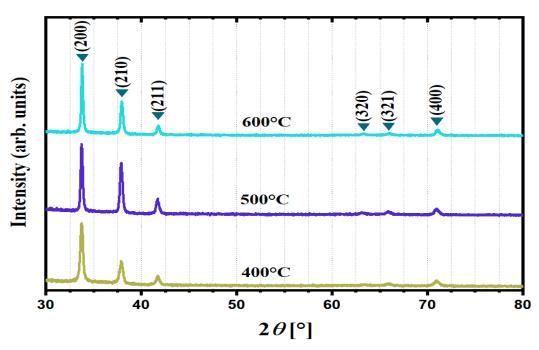


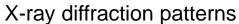
### Upscaling to copper cavities

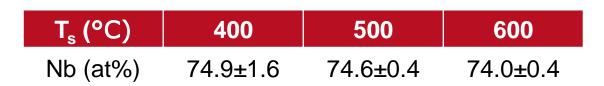


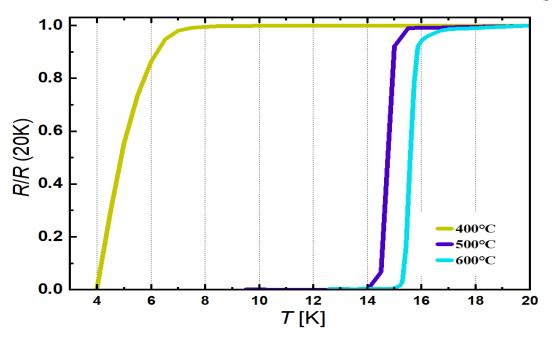
300 nm Nb<sub>3</sub>Sn films grown at different substrate temperature on fused silica substrate











Resistivity normalized to the resistivity at 20 K

Sputtering parameters:

DC sputtering

 $I_{Nb} = 450 \text{ mA}$ 

 $I_{Sn} = 80 \text{ mA}$ 

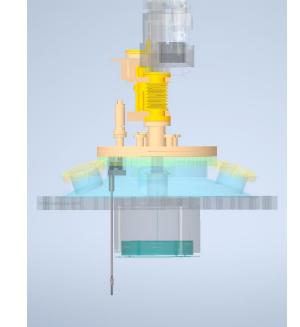
**Amir Farhood** 

## **TOSCA** co-operation





- Disc coating (for Hamburg)
- Antenna coating with Nb<sub>3</sub>Sn (for Mainz)



New top cover with Z-shift for the antenna coating

# Nb<sub>3</sub>Sn cavity roadmap



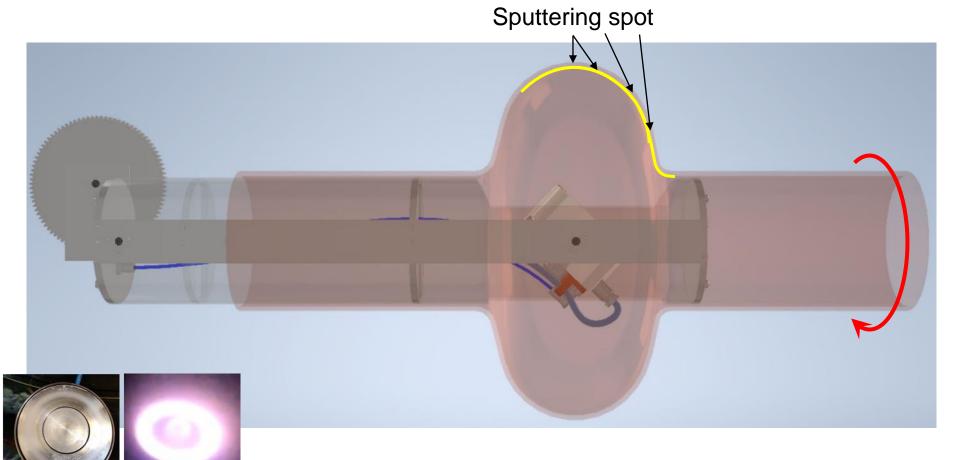


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# **Cavity sputtering**







In cooperation with Fraunhofer FEP, Dresden

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